

N-Channel Super Junction Power MOSFET III

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent R_{DS(ON)} with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

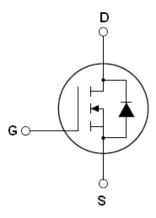
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- ●Small package
- ●Ultra Low Gate Charge cause lower driving requirements
- ●100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

V _{DS}	800	V
R _{DS(ON)TYP}	480	mΩ
I_{D}	9	A



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
NCE80T560D	TO-263	NCE80T560D
NCE80T560	TO-220	NCE80T560
NCE80T560F	TO-220F	NCE80T560F







TO-263

TO-220

TO-220F

Table 1. Absolute Maximum Ratings (T_c=25℃)

Parameter	Symbol	NCE80T560D NCE80T560	NCE80T560F	Unit
Drain-Source Voltage (V _{GS} =0V)	V _{DS}	800		V
Gate-Source Voltage (VDS=0V) AC (f>1 Hz)	V _{GS}	土	30	V
Continuous Drain Current at Tc=25°C	I _{D (DC)}	9	9*	Α
Continuous Drain Current at Tc=100°C	I _{D (DC)}	6	6*	Α
Pulsed drain current (Note 1)	I _{DM (pluse)}	36	36*	Α
Maximum Power Dissipation(Tc=25℃)	P _D	131	33.2	W
Derate above 25°C		1.05	0.265	W/°C
Single pulse avalanche energy (Note 2)	Eas	290		mJ
Avalanche current ^(Note 1)	I _{AR}	2.8		Α
Repetitive Avalanche energy , t_{AR} limited by T_{jmax} (Note 1)	E _{AR}	1.4		mJ



Parameter	Symbol	NCE80T560D NCE80T560	NCE80T560F	Unit
Drain Source voltage slope, V _{DS} ≤480 V,	dv/dt	50		V/ns
Reverse diode dv/dt, V _{DS} ≤480 V,I _{SD} <i<sub>D</i<sub>	dv/dt	15		V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55	+150	°C

^{*} limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	NCE80T560D NCE80T560	NCE80T560F	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R _{thJC}	0.95	3.76	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R _{thJA}	62	80	°C /W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

	Characteristics (TA=25 Cuniess otherwise noted)							
Parameter	Symbol	Condition	Min	Тур	Max	Unit		
On/off states	On/off states							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	800			V		
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =800V,V _{GS} =0V			1	μA		
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =800V,V _{GS} =0V			100	μA		
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±100	nA		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	3	3.5	4	V		
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =4A		480	560	mΩ		
Dynamic Characteristics								
Input Capacitance	C _{lss}	\/ -50\/\/ -0\/		1200	1390	pF		
Output Capacitance	Coss	V_{DS} =50V, V_{GS} =0V, F=1.0MHz		75		pF		
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIDZ		0.3		pF		
Total Gate Charge	Qg	\/ -400\/ -00		25	42	nC		
Gate-Source Charge	Q _{gs}	V_{DS} =480V, I_{D} =9A, V_{GS} =10V		8		nC		
Gate-Drain Charge	Q_{gd}	V _{GS} =10V		8.5		nC		
Switching times								
Turn-on Delay Time	t _{d(on)}			16		nS		
Turn-on Rise Time	t _r	V _{DD} =480V,I _D =5A,		11		nS		
Turn-Off Delay Time	t _{d(off)}	$R_G=2.3\Omega, V_{GS}=10V$		58		nS		
Turn-Off Fall Time	t _f			10		nS		
Source- Drain Diode Characteristics								
Source-drain current(Body Diode)	I _{SD}	T _C =25°C			9	Α		
Pulsed Source-drain current(Body Diode)	I _{SDM}	1c=25 C			36	Α		
Forward On Voltage	V_{SD}	Tj=25°C,I _{SD} =9A,V _{GS} =0V		0.9	1.2	V		
Reverse Recovery Time	t _{rr}			240		nS		
Reverse Recovery Charge	Q _{rr}	Tj=25°C,I _F =5A,di/dt=100A/μs		1.1		uC		
Peak Reverse Recovery Current	I _{rrm}			9		Α		

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25°C,VDD=50V,VG=10V, R_G=25 Ω



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure 1. Safe operating area

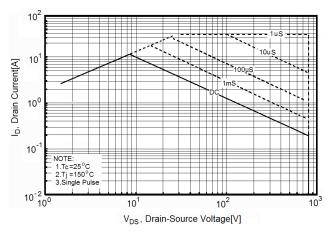


Figure 3. Source-Drain Diode Forward Voltage

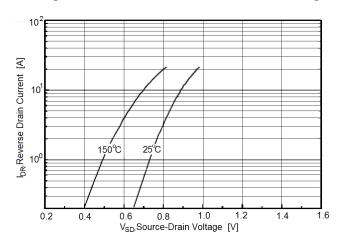


Figure 5. Transfer characteristics

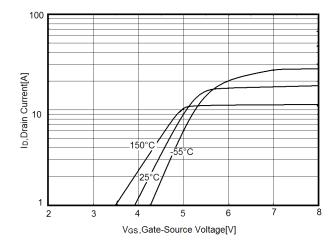


Figure 2. Safe operating area for TO-220F

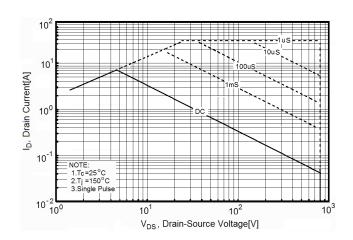


Figure 4. Output characteristics

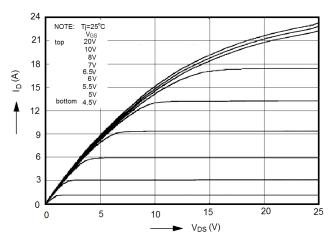


Figure 6. Static drain-source on resistance

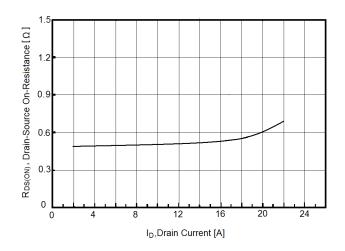




Figure 7. R_{DS(ON)} vs Junction Temperature

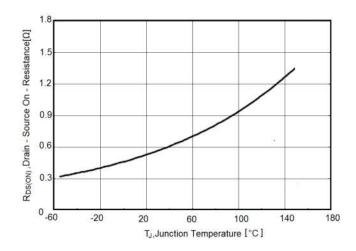


Figure8. BV_{DSS} vs Junction Temperature

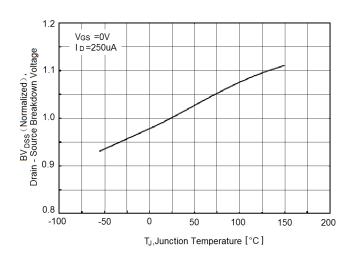


Figure 9. Maximum ID vs Junction Temperature

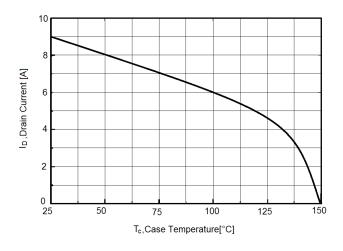


Figure 10. Gate charge waveforms

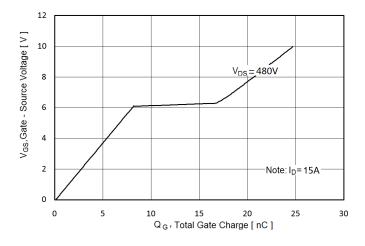


Figure 11. Capacitance

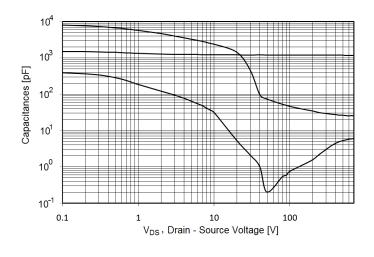


Figure 12. Transient Thermal Impedance

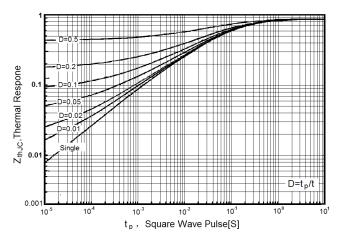
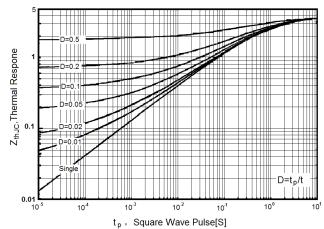




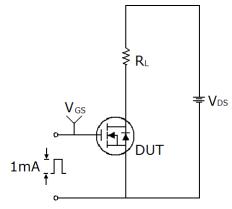
Figure 13. Transient Thermal Impedance for TO-220F

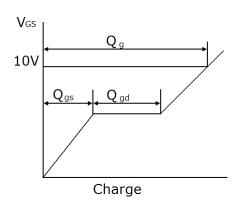




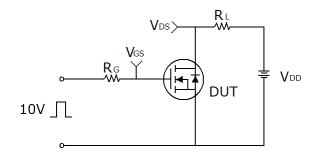
Test circuit

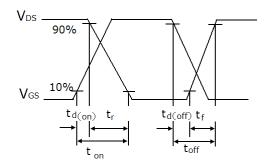
1) Gate charge test circuit & Waveform



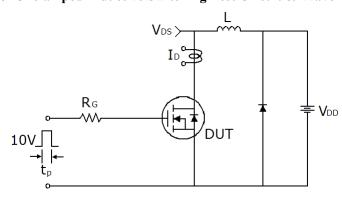


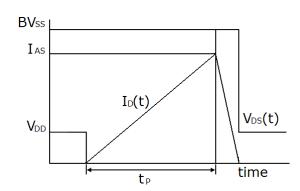
2) Switch Time Test Circuit:





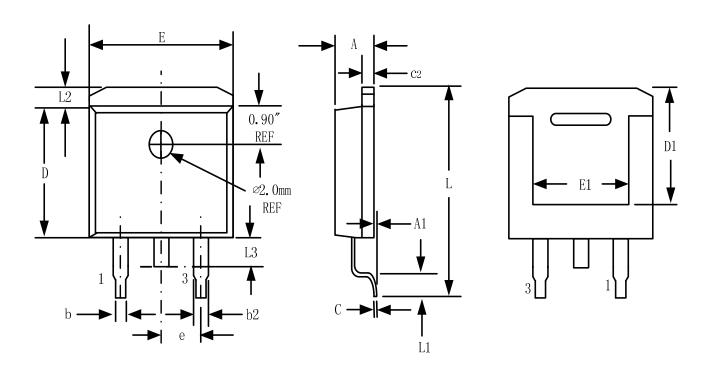
3) Unclamped Inductive Switching Test Circuit & Waveforms







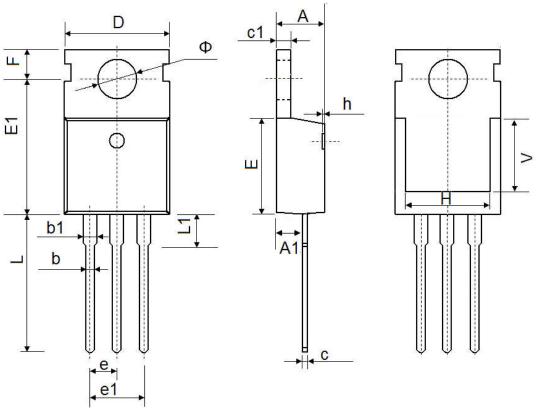
TO-263-3L Package Information



Symph of	Dimensions	In Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
А	4.32	4.57	0.170	0.180
A1	-	0.25		0.010
b	0.71	0.94	0.028	0.037
b2	1.15	1.40	0.045	0.055
С	0.46	0.61	0.018	0.024
c2	1.22	1.40	0.048	0.055
D	8.89	9.40	0.350	0.370
D1	8.01	8.23	0.315	0.324
E	10.04	10.28	0.395	0.405
E1	7.88	8.08	0.310	0.318
е	2.54	BSC	0.100	BSC
L	14.73	15.75	0.580	0.620
L1	2.29	2.79	0.090	0.110
L2	1.15	1.39	0.045	0.055
L3	1.27	1.77	0.050	0.070



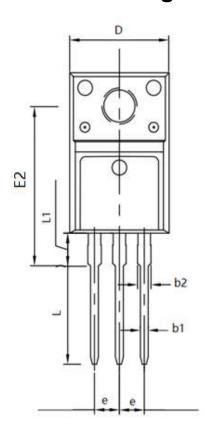
TO-220-3L-C Package Information

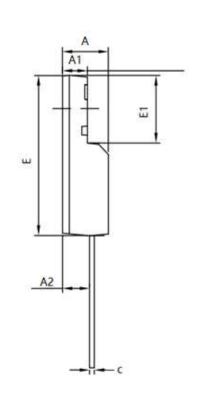


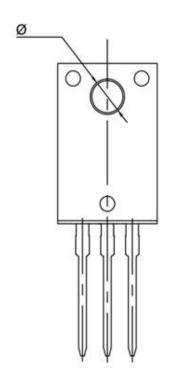
Comple of	Dimensions	s In Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
С	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
е	2.54	IO TYP.	0.100	TYP.
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
Н	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.50	00 REF.	0.295	REF.
Ф	3.400	3.800	0.134	0.150



TO-220F Package Information







Symbol	Dimensions	n Millimeters	Dimension	s In Inches
	Min.	Max.	Min.	Max.
А	4.500	4.900	0.177	0.193
A1	2.340	2.740	0.092	0.108
A2	2.560	2.960	0.101	0.117
b1	0.700	0.900	0.028	0.035
b2	1.180	1.580	0.046	0.062
С	0.400	0.600	0.016	0.024
D	9.960	10.360	0.392	0.408
Е	15.670	15.970	0.617	0.629
E1	6.500	6.900	0.256	0.272
E2	15.500	16.100	0.610	0.634
е	2.540	2.540 TYP) TYP
Ф	3.080	3.280	0.121	0.129
L	12.640	13.240	0.498	0.521
L1	3.030	3.430	0.119	0.135



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